



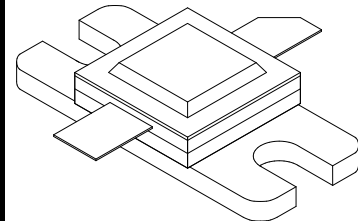
## MDS60L

60 Watts, 50 Volts, Pulsed  
Avionics 1030 - 1090 MHz

### GENERAL DESCRIPTION

The MDS60L is a high power COMMON BASE bipolar transistor. It is designed for MODE-S ELM systems in the 1030 - 1090 MHz frequency band. The transistor includes a double input prematch for broadband performance. The device has gold thin-film metallization and diffused ballasting in a hermetically sealed package for proven highest MTTF.

### CASE OUTLINE 55AW Style 1



### ABSOLUTE MAXIMUM RATINGS

#### Maximum Power Dissipation

Device Dissipation @25°C<sup>1</sup> 120 W

#### Maximum Voltage and Current

Collector to Emitter Voltage (BV<sub>ces</sub>) 65 V

Emitter to Base Voltage (BV<sub>ebo</sub>) 3.5 V

Peak Collector Current (I<sub>c</sub>) 4 A

#### Maximum Temperatures

Storage Temperature -65 to +150 °C

Operating Junction Temperature +200 °C

### ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P <sub>out</sub>	Power Out	F = 1030, 1090 MHz	60			W
P <sub>in</sub>	Power Input	V <sub>cc</sub> = 50 Volts			6	W
P <sub>g</sub>	Power Gain	PW = Note 2	10			dB
η <sub>c</sub>	Collector Efficiency	DF = Note 2		34		%
VSWR	Load Mismatch Tolerance				2:1	
Pd <sup>1</sup>	Pulse Droop				0.8	dB
Trise <sup>1</sup>	Rise Time				100	nSec

### FUNCTIONAL CHARACTERISTICS @ 25°C

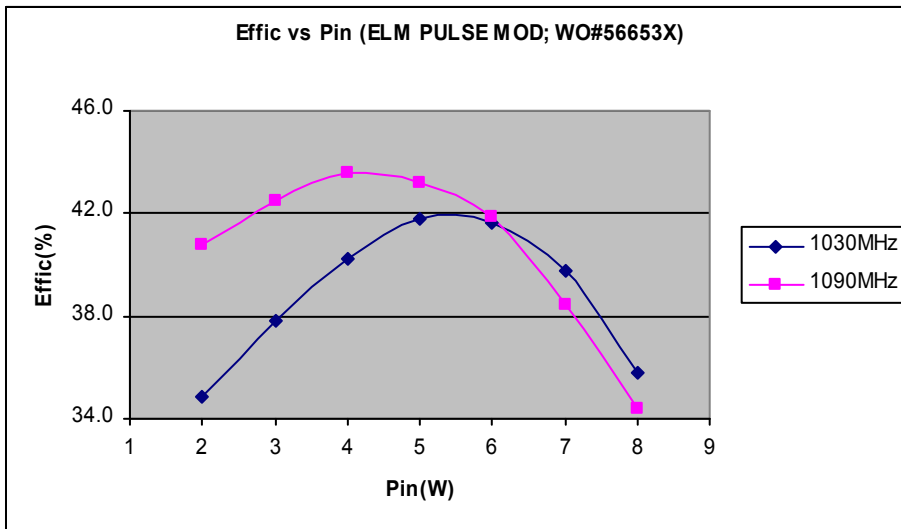
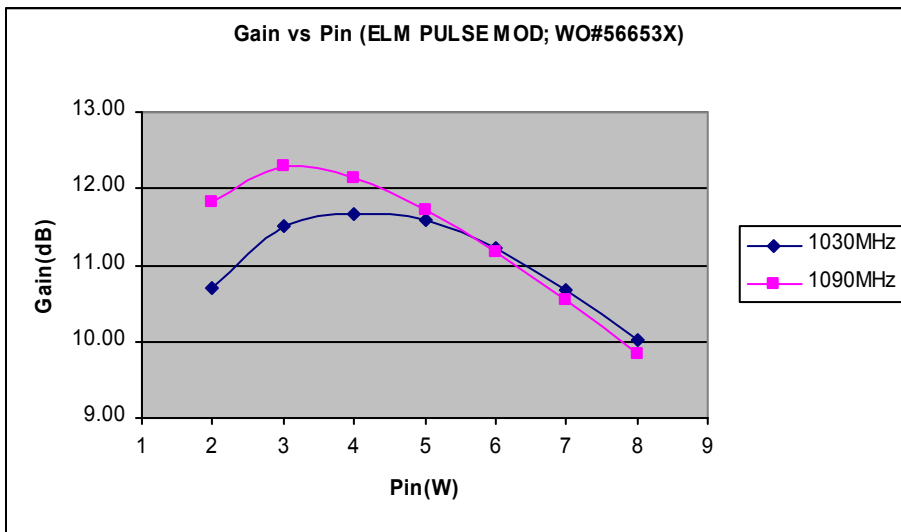
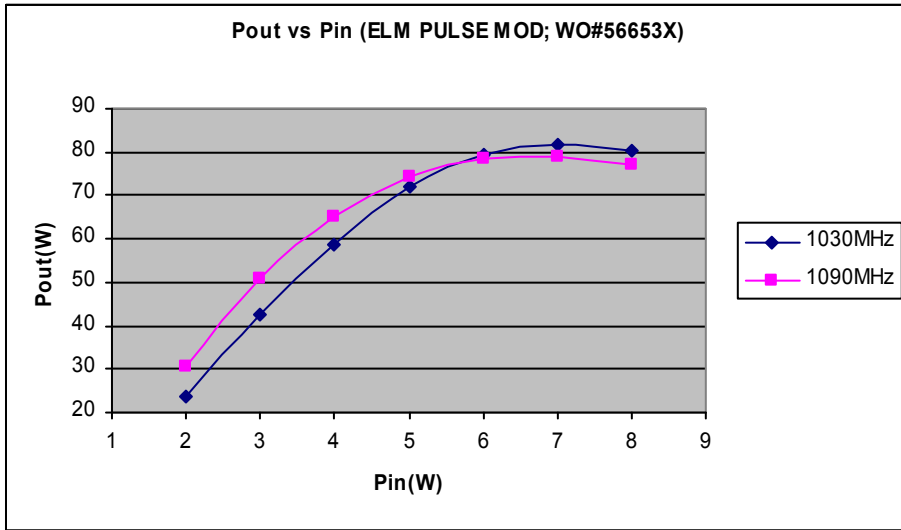
BV <sub>ebo</sub>	Emitter to Base Breakdown	I <sub>e</sub> = 5 mA	3.5			V
BV <sub>ces</sub>	Collector to Emitter Breakdown	I <sub>c</sub> = 25 mA	65			V
BV <sub>cbo</sub>	Collector to Base Breakdown	I <sub>c</sub> = 25 mA	65			V
h <sub>FE</sub>	DC – Current Gain	V <sub>ce</sub> = 5V, I <sub>c</sub> = 500 mA	20			
θ <sub>jc</sub> <sup>1</sup>	Thermal Resistance				0.5	°C/W

NOTE 1: AT RATED OUTPUT POWER AND PULSE CONDITIONS

NOTE 2: ELM Burst: 32μSec ON/ 18μSec OFF x 48, repeated at 23mSec

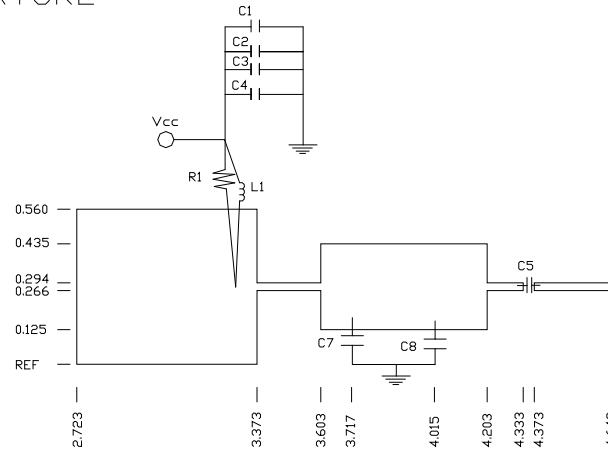
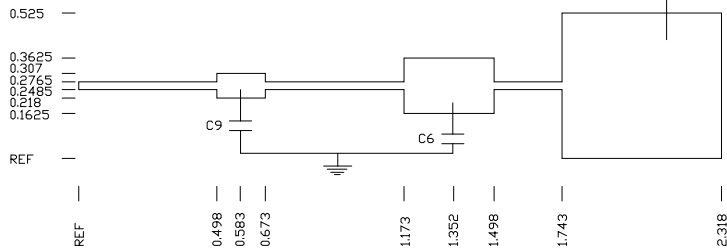
Rev C: Updated June 2011

MDS60L SAMPLE RF DATA (SN#2-8; WO#56653X)



# MDS60L TEST FIXTURE

C1=1000uF electrolytic cap  
 C2=100uF electrolytic cap  
 C3=0.1uF chip cap  
 C4=C5=82pF chip cap  
 C6=1.5pF chip cap  
 C7=C8=0.5pF chip cap  
 C9=0.5pF chip cap  
 R1=4.2 ohm resistor  
 L1=3 turn, #22 wire  
 L2=585mil, #18 wire  
 Dielectric: Er=2.3; H=10mils



NOTE: Dimensions in Inches

MDS60L

